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(71) Applicant: **LAM RESEARCH CORPORATION**
[US/US]; 4650 Cushing Pkwy., Fremont, California 94538 (US).

(72) Inventors: **LI, Da**; 4650 Cushing Pkwy., Fremont, California 94538 (US). **KIM, Ji Yeon**; 4650 Cushing Pkwy., Fremont, California 94538 (US). **TAN, Samantha S.H.**; 4650 Cushing Pkwy., Fremont, California 94538 (US). **WEIDMAN, Timothy William**; 4650 Cushing Pkwy., Fremont, California 94538 (US).

(74) Agent: **RAMESH, Elaine M.** et al.; Weaver Austin Villeneuve & Sampson LLP, P.O. Box 70250, Oakland, California 94612-0250 (US).

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(54) Title: CYCLIC DEVELOPMENT OF METAL OXIDE BASED PHOTORESIST FOR ETCH STOP DETERRENCE

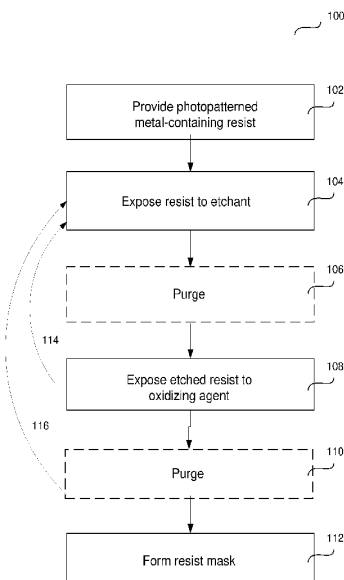


FIG. 1

(57) Abstract: Provided are processes for development of photopatterned metal or metal oxide-based thin film photoresists post-EUV exposure for removal of non-volatile species and deterring etch stop. Repeated cycles of alternating treatment with an etchant and an oxidizing agent; or treatment with an etchant followed by treatment with a wash agent are effective techniques for removal of the undesired unexposed portion of a photoresist.

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